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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100lfdfb-30

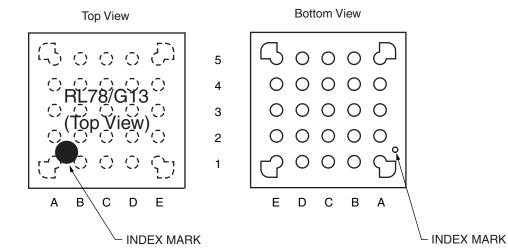
Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

1.3.3 25-pin products

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• 25-pin plastic WFLGA (3 × 3 mm, 0.50 mm pitch)



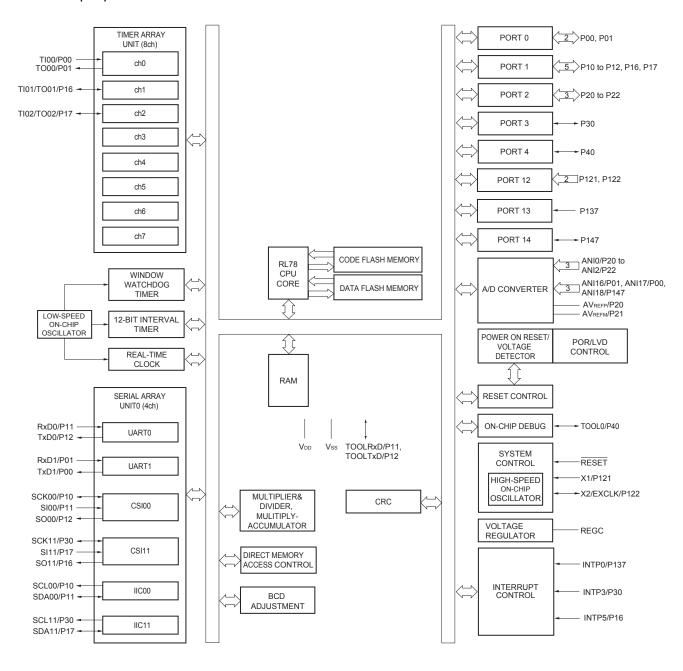
	Α	В	С	D	E	
5	P40/TOOL0	RESET	P01/ANI16/ TO00/RxD1	P22/ANI2	P147/ANI18	5
4	P122/X2/ EXCLK	P137/INTP0	P00/ANI17/ TI00/TxD1	P21/ANI1/ AVREFM	P10/SCK00/ SCL00	4
3	P121/X1	V _{DD}	P20/ANI0/ AV _{REFP}	P12/SO00/ TxD0/ TOOLTxD	P11/SI00/ RxD0/ TOOLRxD/ SDA00	3
2	REGC	Vss	P30/INTP3/ SCK11/SCL11	P17/Tl02/ TO02/SO11	P50/INTP1/ SI11/SDA11	2
1	P60/SCLA0	P61/SDAA0	P31/TI03/ TO03/INTP4/ PCLBUZ0	P16/TI01/ TO01/INTP5	P130	1
	A	В	С	D	E	

Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

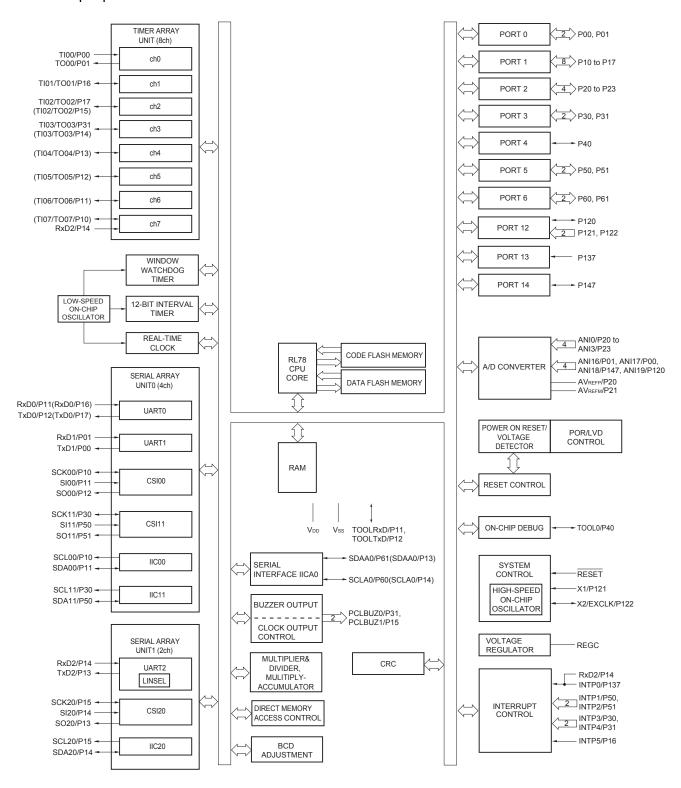
Remark For pin identification, see **1.4 Pin Identification**.

1.5 Block Diagram

1.5.1 20-pin products

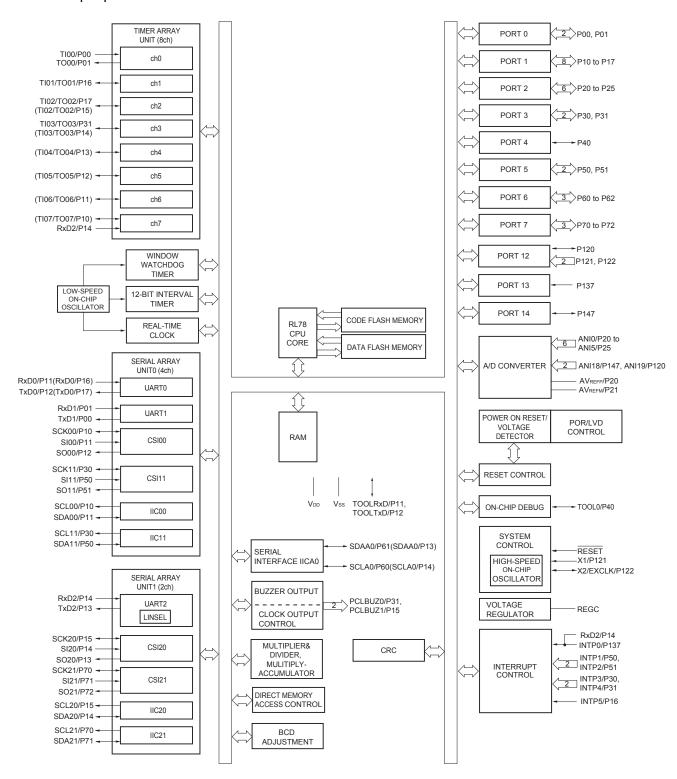


1.5.4 30-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.5.6 36-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

(3) 128-pin products, and flash ROM: 384 to 512 KB of 44- to 100-pin products

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V) (1/2)

Parameter	Symbol			Conditions	,	_	MIN.	TYP.	MAX.	Unit
Supply current Note 1	I _{DD1}	Operating	HS (high-	fih = 32 MHz Note 3	Basic	V _{DD} = 5.0 V		2.6		mA
current		mode	speed main) mode Note 5		operation	$V_{DD} = 3.0 \text{ V}$		2.6		mA
					Normal	$V_{DD} = 5.0 \text{ V}$		6.1	9.5	mA
					operation	$V_{DD} = 3.0 \text{ V}$		2.6	9.5	mA
				main) $f_{IH} = 4 \text{ MHz}^{\text{Note 3}}$ node $f_{IH} = 4 \text{ MHz}^{\text{Note 3}}$ $f_{IH} = 4 \text{ MHz}^{\text{Note 3}}$ $f_{IH} = 4 \text{ MHz}^{\text{Note 2}},$ $V_{DD} = 5.0 \text{ V}$ $f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	$V_{DD} = 5.0 \text{ V}$		4.8	7.4	mA
					operation	$V_{DD} = 3.0 \text{ V}$		4.8	7.4	mA
				$f_{IH} = 16 \text{ MHz}^{Note 3}$	Normal	$V_{DD} = 5.0 \text{ V}$		3.5	5.3	mA
					operation	$V_{DD} = 3.0 \text{ V}$		3.5	5.3	mA
			LS (low-	$f_{IH} = 8 \text{ MHz}^{Note 3}$	Nomal	$V_{DD} = 3.0 \text{ V}$		1.5	2.3	mA
			speed main) mode Note 5		operation	V _{DD} = 2.0 V		1.5	2.3	mA
			LV (low-	$f_{IH} = 4 \text{ MHz}^{Note 3}$	Normal	V _{DD} = 3.0 V		1.5	2.0	mA
			voltage main) mode		operation	V _{DD} = 2.0 V		1.5	2.0	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.9	6.1	mA
			speed main) mode Note 5		operation	Resonator connection		4.1	6.3	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Nomal	Square wave input		3.9	6.1	mA
				$V_{DD} = 3.0 \text{ V}$	operation	Resonator connection		4.1	6.3	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		2.5	3.7	mA
				$V_{DD} = 5.0 \text{ V}$	operation	Resonator connection		2.5	3.7	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		2.5	3.7	mA
			LS (low- speed main) mode Note 5	$V_{DD} = 3.0 \text{ V}$	operation	Resonator connection		2.5	3.7	mA
				$f_{MX} = 8 MHz^{Note 2}$	Nomal	Square wave input		1.4	2.2	mA
				$V_{DD} = 3.0 \text{ V}$	operation	Resonator connection		1.4	2.2	mA
				$f_{MX} = 8 MHz^{Note 2}$	Nomal	Square wave input		1.4	2.2	mA
				$V_{DD} = 2.0 \text{ V}$	operation	Resonator connection		1.4	2.2	mA
			Subsystem	fsub = 32.768 kHz	Nomal	Square wave input		5.4	6.5	μΑ
			clock operation	T _A = -40°C	operation	Resonator connection		5.5	6.6	μΑ
				fsub = 32.768 kHz	Nomal	Square wave input		5.5	6.5	μΑ
				T _A = +25°C	operation	Resonator connection		5.6	6.6	μΑ
				fsub = 32.768 kHz	Nomal	Square wave input		5.6	9.4	μΑ
				TA = +50°C	operation	Resonator connection		5.7	9.5	μΑ
				fsuB = 32.768 kHz	Normal	Square wave input		5.9	12.0	μΑ
				Note 4 $T_A = +70^{\circ}C$	operation	Resonator connection		6.0	12.1	μΑ
				fsuв = 32.768 kHz	Normal	Square wave input		6.6	16.3	μΑ
				Note 4 $T_A = +85^{\circ}C$	operation	Resonator connection		6.7	16.4	μΑ

(Notes and Remarks are listed on the next page.)



(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \leq \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	C	Conditions	HS (high main)	•	LS (low main)	•	main) Mode MIN. MAX. 1000 1000 1000 1000 1000 tkcy1/2 - 50 tkcy1/2 - 50 tkcy1/2 - 50 tkcy1/2 - 100 tkcy1/2 - 100	Unit	
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tксү1 ≥ 4/fс∟к	$2.7~V \leq EV_{DD0} \leq 5.5$ V	125		500		1000		ns
			$2.4~V \leq EV_{DD0} \leq 5.5$ V	250		500		1000		ns
			$1.8~V \le EV_{DD0} \le 5.5$ V	500		500		1000		ns
			$1.7~V \le EV_{DD0} \le 5.5$ V	1000		1000		1000		ns
			$1.6~V \le EV_{DD0} \le 5.5$ V	_		1000		1000		ns
SCKp high-/low-level width	tkhi, tkli	4.0 V ≤ EV _D	00 ≤ 5.5 V	tксү1/2 – 12		tксу1/2 — 50				ns
		2.7 V ≤ EV _D	oo ≤ 5.5 V	tксү1/2 – 18		tксу1/2 — 50				ns
		$2.4~\text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5~\text{V}$		tксү1/2 – 38		tксу1/2 — 50				ns
		1.8 V ≤ EV _D	00 ≤ 5.5 V	tксү1/2 — 50		tксү1/2 — 50				ns
		1.7 V ≤ EV _D	00 ≤ 5.5 V	tксу1/2 — 100		tксу1/2 — 100				ns
		1.6 V ≤ EVD	₀₀ ≤ 5.5 V	_		tксу1/2 — 100				ns
SIp setup time	tsıĸı	4.0 V ≤ EV _{DI}	00 ≤ 5.5 V	44		110		110		ns
(to SCKp↑)		2.7 V ≤ EV _{DI}	00 ≤ 5.5 V	44		110		110		ns
		2.4 V ≤ EV _{DI}	00 ≤ 5.5 V	75		110		110		ns
		1.8 V ≤ EV _{DI}	oo ≤ 5.5 V	110		110		110		ns
		1.7 V ≤ EV _{DI}	oo ≤ 5.5 V	220		220		220		ns
		1.6 V ≤ EV _{DI}	oo ≤ 5.5 V	_		220		220		ns
SIp hold time	tksi1	1.7 V ≤ EV _{DI}	00 ≤ 5.5 V	19		19		19		ns
(from SCKp↑) Note 2		1.6 V ≤ EV _{DI}	00 ≤ 5.5 V	_		19		19		ns
Delay time from SCKp↓ to SOp	tkso1	$1.7 \text{ V} \le \text{EV}_{DI}$ $C = 30 \text{ pF}^{\text{Note}}$			25		25		25	ns
output Note 3		$1.6 \text{ V} \leq \text{EV}_{DI}$ $C = 30 \text{ pF}^{\text{Note}}$			_		25		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DD0} < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

$$\label{eq:maximum transfer rate} \text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \text{ln } (1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.0}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
- 5. Use it with $EV_{DD0} \ge V_b$.
- **6.** The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 1.8 V \leq EV_{DD0} < 3.3 V and 1.6 V \leq V_b \leq 2.0 V

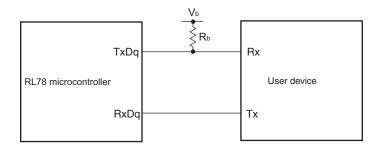
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln \ (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **7.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)





(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (2/2)

Parameter	Symbol	Conditions	speed	high- main) ode			,	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp high-/low-level width	tкн2, tкL2	$\begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V \end{aligned}$	tксу2/2 - 12		tkcy2/2 - 50		txcy2/2 - 50		ns
		$\begin{aligned} 2.7 & \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 & \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V} \end{aligned}$	tkcy2/2 - 18		tксү2/2 - 50		tkcy2/2 - 50		ns
		$\begin{aligned} 1.8 \ V &\leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note 2}} \end{aligned}$	tkcy2/2 - 50		tксү2/2 - 50		tkcy2/2 - 50		ns
SIp setup time (to SCKp↑) Note 3	tsık2	$\begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V \end{aligned}$	1/fмск + 20		1/fмск + 30		1/fмcк + 30		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$	1/fмск + 20		1/fмск + 30		1/fmck + 30		ns
		$\begin{aligned} 1.8 \ V &\leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note 2}} \end{aligned}$	1/fмск + 30		1/fмск + 30		1/fмcк + 30		ns
SIp hold time (from SCKp↑) Note 4	tksi2		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
Delay time from SCKp↓ to SOp output Note 5	tkso2	$4.0~V \leq EV_{DD0} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0$ $V,$ $C_b = 30~pF,~R_b = 1.4~k\Omega$		2/fмск + 120		2/fмск + 573		2/fмск + 573	ns
		$2.7 \; V \leq EV_{DD0} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7$ $V,$ $C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega$		2/fмск + 214		2/fмск + 573		2/fмск + 573	ns
		$\begin{split} 1.8 \ V &\leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_b \leq 2.0 \ V^{\text{Note 2}}, \\ C_b &= 30 \ pF, \ R_b = 5.5 \ k\Omega \end{split}$		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns

Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

- 2. Use it with $EV_{DD0} \ge V_b$.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **5.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

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2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$



 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (4/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ loh1 = -3.0 mA	EV _{DD0} – 0.7			V
		P90 to P97, P100 to P106, P110 to	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $I_{\text{OH1}} = -2.0 \text{ mA}$	EV _{DD0} – 0.6			V
		P117, P120, P125 to P127, P130, P140 to P147	$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $I_{\text{OH1}} = -1.5 \text{ mA}$	EV _{DD0} – 0.5		0.7 0.6 0.4 0.4 2.0 0.4	V
	V _{OH2}	P20 to P27, P150 to P156	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH2} = -100 \ \mu \text{ A}$	V _{DD} – 0.5			V
Output voltage, low	P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87,	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 8.5~mA$			0.7	V	
		P90 to P97, P100 to P106, P110 to	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 3.0~mA$			0.6	V
		P140 to P147	$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 1.5~mA$			0.4	V
			$2.4~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 0.6~mA$			0.4	٧
	V _{OL2}	P20 to P27, P150 to P156	$2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V},$ $\text{Io}_{L2} = 400 \ \mu \text{ A}$			0.4	V
	Vоьз	P60 to P63	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 15.0~mA$			2.0	V
			$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 5.0~mA$			0.4	V
			$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 3.0~mA$			0.4	V
			$2.4~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 2.0~mA$			0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-spee	ed main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V$	250		ns
			$2.4~V \leq EV_{DD0} \leq 5.5~V$	500		ns
SCKp high-/low-level width	t кн1,	4.0 V ≤ EV _{DD}	₀₀ ≤ 5.5 V	tkcy1/2 - 24		ns
	t _{KL1}	2.7 V ≤ EV _{DD}	₀₀ ≤ 5.5 V	tkcy1/2 - 36		ns
		2.4 V ≤ EV _{DD}	₀₀ ≤ 5.5 V	tkcy1/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	tsıĸ1	4.0 V ≤ EV _{DD}	₀₀ ≤ 5.5 V	66		ns
		2.7 V ≤ EV _{DD}	₀₀ ≤ 5.5 V	66		ns
		2.4 V ≤ EV _{DD}	₀₀ ≤ 5.5 V	113		ns
SIp hold time (from SCKp↑) Note 2	t KSI1			38		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 30 pF Note	o 4		50	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3).
 - g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)
 - 2. fmck: Serial array unit operation clock frequency
 - (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 - n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (simplified I²C mode)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-sp Mo	,	Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$		400 Note1	kHz
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$		100 Note1	kHz
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Hold time when SCLr = "L"	tLOW	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	1200		ns
		$C_b = 50$ pF, $R_b = 2.7$ k Ω			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Hold time when SCLr = "H"	tніgн	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	1200		ns
		$C_b = 50$ pF, $R_b = 2.7$ k Ω			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Data setup time (reception)	tsu:dat	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	1/fмск + 220		ns
		$C_b = 50$ pF, $R_b = 2.7$ k Ω	Note2		
		$2.4~V \leq EV_{DD} \leq 5.5~V,$	1/fмск + 580		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	Note2		
Data hold time (transmission)	thd:dat	$2.7~V \leq EV_{DD0} \leq 5.5~V,$	0	770	ns
		$C_b = 50$ pF, $R_b = 2.7$ k Ω			
		$2.4~V \leq EV_{DD0} \leq 5.5~V,$	0	1420	ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			

Notes 1. The value must also be equal to or less than fmck/4.

2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol		Conditio	ns	` `	speed main) ode	Unit
					MIN.	MAX.	
Transfer rate		Reception	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$			fmck/12 Note 1	bps
			V , $2.7 \ V \le V_b \le 4.0 \ V$	Theoretical value of the maximum transfer rate fclk = 32 MHz, fmck = fclk		2.6	Mbps
			$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0$			fmck/12 Note 1	bps
			$V,$ $2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate fclk = 32 MHz, fmck = fclk		2.6	Mbps
			$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V},$			fMCK/12 Notes 1,2	bps
			$1.6~V \leq V_b \leq 2.0~V$	Theoretical value of the maximum transfer rate fclk = 32 MHz, fmck = fclk		2.6	Mbps

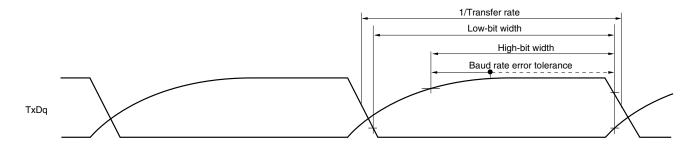
- Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.
 - 2. The following conditions are required for low voltage interface when EVDDO < VDD.

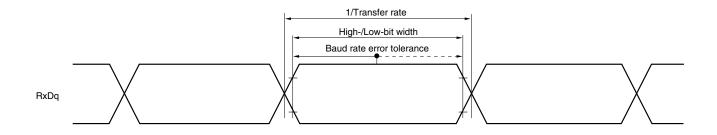
 $2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$: MAX. 1.3 Mbps

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

- Remarks 1. V_b[V]: Communication line voltage
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03, 10 to 13)
 - **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

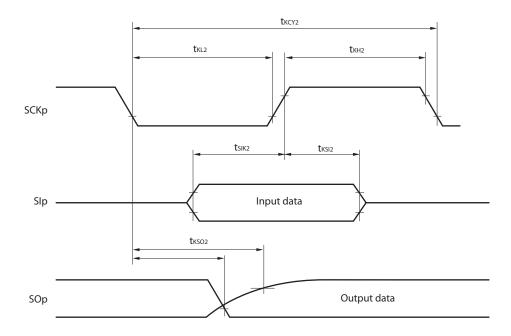
UART mode bit width (during communication at different potential) (reference)



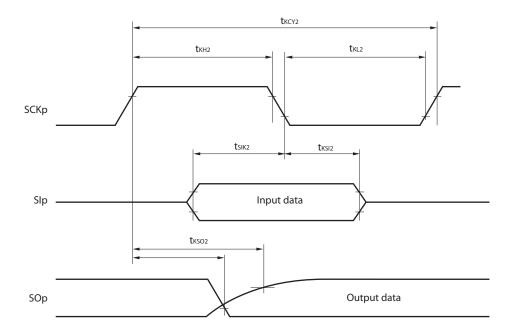


- $\begin{tabular}{ll} \textbf{Remarks 1.} & R_b[\Omega]: Communication line (TxDq) pull-up resistance, \\ & C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage \\ \end{tabular}$
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 - **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12. 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	Conditions	s	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall errorNote 1	AINL	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANIO to ANI14,	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
		ANI16 to ANI26	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μS
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal reference	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μS
		voltage, and temperature sensor output voltage (HS	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μS
		(high-speed main) mode)					
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Full-scale errorNotes 1, 2	Ers	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±4.0	LSB
Differential linearity error	DLE	10-bit resolution	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI14		0		V _{DD}	V
		ANI16 to ANI26		0		EV _{DD0}	V
		Internal reference voltage outpotential (2.4 V \leq VDD \leq 5.5 V, HS (high-		VBGR Note 3		V	
		Temperature sensor output vo $(2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, HS (high-$	· ·	,	VTMPS25 Note 3	3	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

3.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(Ta = -40 to +105°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	V _{LVD0}	Power supply rise time	3.90	4.06	4.22	V
voltage			Power supply fall time	3.83	3.98	4.13	V
		V _{LVD1}	Power supply rise time	3.60	3.75	3.90	V
			Power supply fall time	3.53	3.67	3.81	V
		V _{LVD2}	Power supply rise time	3.01	3.13	3.25	V
			Power supply fall time	2.94	3.06	3.18	V
		V LVD3	Power supply rise time	2.90	3.02	3.14	V
			Power supply fall time	2.85	2.96	3.07	V
		V _{LVD4}	Power supply rise time	2.81	2.92	3.03	V
			Power supply fall time	2.75	2.86	2.97	V
		V _{LVD5}	Power supply rise time	2.70	2.81	2.92	V
			Power supply fall time	2.64	2.75	2.86	V
		V _{LVD6}	Power supply rise time	2.61	2.71	2.81	V
			Power supply fall time	2.55	2.65	2.75	V
		V _{LVD7}	Power supply rise time	2.51	2.61	2.71	V
			Power supply fall time	2.45	2.55	2.65	V
Minimum p	ulse width	tLW		300			μS
Detection d	elay time					300	μS

LVD Detection Voltage of Interrupt & Reset Mode

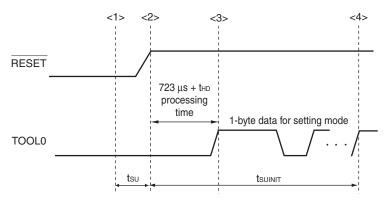
(Ta = -40 to +105°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol	Co	nditions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	V _{LVDD0}	VPOC2, VPOC1, VPOC0 = 0, 1	1, falling reset voltage	2.64	2.75	2.86	V
mode	VLVDD1	LVIS1, LVIS0 = 1,	O Rising release reset voltage	2.81	2.92	3.03	V
			Falling interrupt voltage	2.75	2.86	2.97	V
	V _{LVDD2}	LVIS1, LVIS0 = 0,	1 Rising release reset voltage	2.90	3.02	3.14	V
			Falling interrupt voltage	2.85	2.96	3.07	V
	V _L VDD3	LVIS1, LVIS0 = 0,	O Rising release reset voltage	3.90	4.06	4.22	V
			Falling interrupt voltage	3.83	3.98	4.13	V

3.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μS
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)		POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

 t_{SU} : Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

4.8 44-pin Products

R5F100FAAFP, R5F100FCAFP, R5F100FDAFP, R5F100FEAFP, R5F100FFAFP, R5F100FGAFP,

R5F100FHAFP, R5F100FJAFP, R5F100FKAFP, R5F100FLAFP

R5F101FAAFP, R5F101FCAFP, R5F101FDAFP, R5F101FEAFP, R5F101FFAFP, R5F101FGAFP,

R5F101FHAFP, R5F101FJAFP, R5F101FKAFP, R5F101FLAFP

R5F100FADFP, R5F100FCDFP, R5F100FDDFP, R5F100FEDFP, R5F100FFDFP, R5F100FGDFP,

R5F100FHDFP, R5F100FJDFP, R5F100FKDFP, R5F100FLDFP

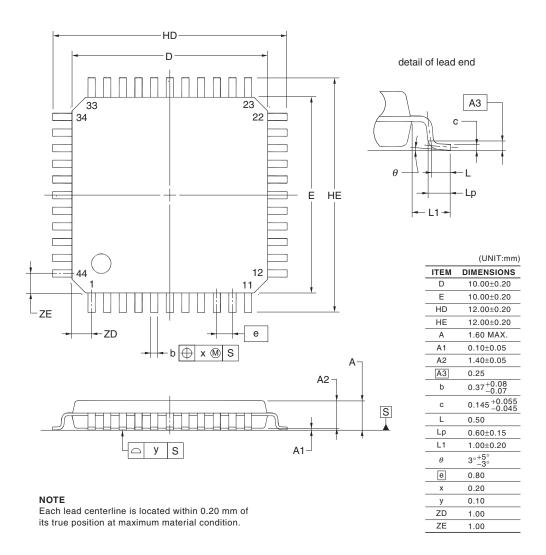
R5F101FADFP, R5F101FCDFP, R5F101FDDFP, R5F101FEDFP, R5F101FFDFP, R5F101FGDFP,

R5F101FHDFP, R5F101FJDFP, R5F101FKDFP, R5F101FLDFP

R5F100FAGFP, R5F100FCGFP, R5F100FDGFP, R5F100FEGFP, R5F100FFGFP, R5F100FGGFP,

R5F100FHGFP, R5F100FJGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP44-10x10-0.80	PLQP0044GC-A	P44GB-80-UES-2	0.36



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			Description		
Rev.	Date	Page	Summary		
3.00	3.00 Aug 02, 2013	163	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (1/2)		
		164, 165	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (2/2)		
		166	Modification of table in 3.5.2 Serial interface IICA		
		166	Modification of IICA serial transfer timing		
		167	Addition of table in 3.6.1 A/D converter characteristics		
		167, 168	Modification of table and notes 3 and 4 in 3.6.1 (1)		
		169	Modification of description in 3.6.1 (2)		
		170	Modification of description and note 3 in 3.6.1 (3)		
		171	Modification of description and notes 3 and 4 in 3.6.1 (4)		
		172	Modification of table and note in 3.6.3 POR circuit characteristics		
		173	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode		
		173	Modification from Supply Voltage Rise Time to 3.6.5 Power supply voltage rising slope characteristics		
		174	Modification of 3.9 Dedicated Flash Memory Programmer Communication (UART)		
		175	Modification of table, figure, and remark in 3.10 Timing Specs for Switching Flash Memory Programming Modes		
3.10	Nov 15, 2013	123	Caution 4 added.		
		125	Note for operating ambient temperature in 3.1 Absolute Maximum Ratings deleted.		
3.30	Mar 31, 2016		Modification of the position of the index mark in 25-pin plastic WFLGA (3 \times 3 mm, 0.50 mm pitch) of 1.3.3 25-pin products		
			Modification of power supply voltage in 1.6 Outline of Functions [20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]		
			Modification of power supply voltage in 1.6 Outline of Functions [40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]		
			Modification of power supply voltage in 1.6 Outline of Functions [80-pin, 100-pin, 128-pin products]		
			ACK corrected to ACK		
			ACK corrected to ACK		

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